

Article

Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition

Heli Seppänen ^{1,*}, Iurii Kim ^{1,2}, Jarkko Etula ³ and Evgeniy Ubyivovk ⁴, Alexei Bouravleuv ^{1,2} and Harri Lipsanen ¹

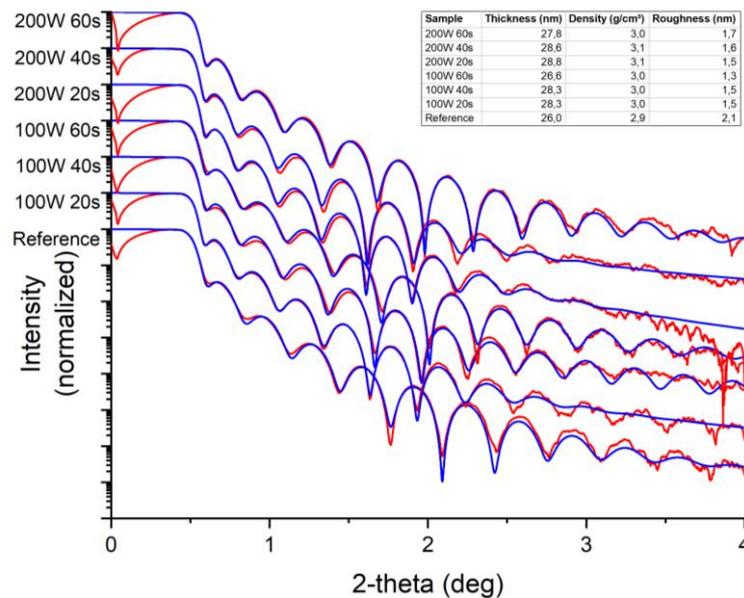


Figure S1. The thickness of the film is in accordance with the approximately 28nm thickness obtained from both ellipsometry and X-ray reflectometry.

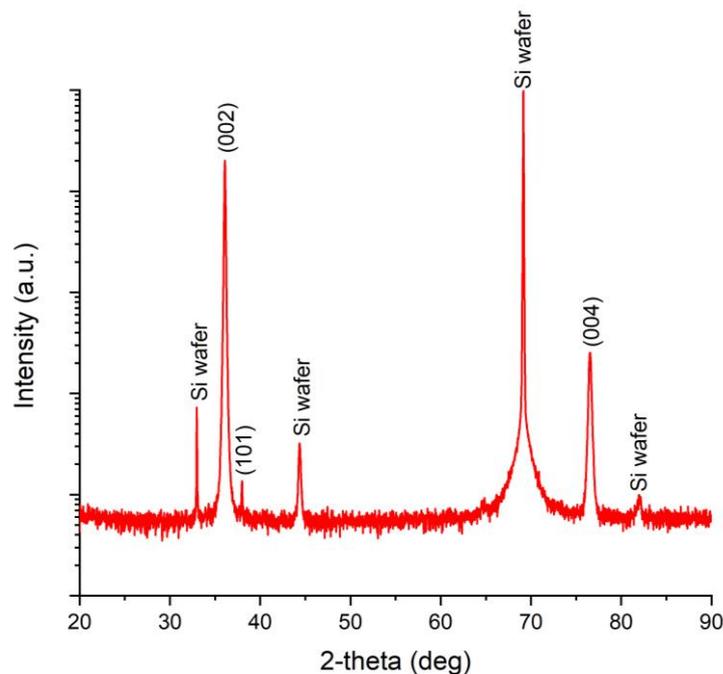


Figure S2. The θ - 2θ XRD pattern of the regrown AlN by MOCVD on top of PEALD template.